

Conductance of the Single Electron Transistor for Arbitrary Tunneling Strength

Georg Göppert¹, Bruno Hüpfer², and Hermann Grabert¹

¹ *Fakultät für Physik, Albert-Ludwigs-Universität,*

Hermann-Herder-Straße 3, D-79104 Freiburg, Germany

² *Chemical Physics Department, Weizmann Institute of Science, 76100 Rehovot, Israel*

(February 1, 2008)

We study the temperature and gate voltage dependence of the conductance of the single electron transistor focusing on highly conducting devices. Electron tunneling is treated nonperturbatively by means of path integral Monte Carlo techniques and the conductance is determined from the Kubo formula. A regularized singular value decomposition scheme is employed to calculate the conductance from imaginary time simulation data. Our findings are shown to bridge between available analytical results in the semiclassical and perturbative limits and are found to explain recent experimental results in a regime not accessible by earlier methods.

73.23.Hk, 73.40.Gk, 73.40.Rw

The single electron transistor (SET) has become a primary device for applications of the Coulomb blockade effect [1]. The modulation of the current in dependence on the gate voltage has been used to build highly sensitive electrometers and thermometers and can serve as switch or amplifier. Since the relative current modulation is most pronounced at small transport voltages where also heating effects become negligible, the quantity of chief interest is the linear conductance. There are two relevant dimensionless parameters [1]: the dimensionless parallel conductance g of the two tunnel junctions measured in units of the conductance quantum $G_K = e^2/h$, and the dimensionless inverse temperature βE_C relating $\beta = 1/k_B T$ with the charging energy E_C . While recent experiments [2–4] have explored a large regime of tunneling conductances and temperatures, available theoretical work is restricted to limiting cases where one of the parameters g or βE_C is small. Approaches for the weakly conducting regime $g \lesssim 1$ [5,6] start in the charge basis and treat tunneling as a weak perturbation, while the semiclassical approach [7,8] starts from the canonically conjugate phase representation and treats small fluctuations about the classical paths which is adequate for $\beta E_C \lesssim 1$. So far no theoretical predictions are available for the regime of highly conducting systems at low temperatures which is within reach of state-of-the-art experiments.

In this work we study the linear conductance of the SET for arbitrary parameters. Electron tunneling is treated nonperturbatively by means of a path integral Quantum Monte Carlo (QMC) approach employed to evaluate the current-current correlation function in imaginary time. We present an improved singular value decomposition (SVD) scheme utilized to determine the conductance via an inverse Laplace transformation. This allows us to obtain results for the entire range of parameters of experimental interest.

Specifically we consider a SET consisting of two tunnel junctions with conductance G_1 , G_2 and capacitance C_1 ,

C_2 , respectively. The junctions in series are biased by a voltage source V and the island between the tunneling barriers is coupled to a gate voltage U_g via a capacitance C_g . From the Kubo formula, we write the dc conductance in terms of the current-current correlation function $F(\tau) = \langle I(\tau)I(0) \rangle$ in imaginary time τ as [8]

$$G = \lim_{\omega \rightarrow 0} \frac{1}{i\hbar\omega} \lim_{i\nu_n \rightarrow \omega + i\delta} \int_0^{\hbar\beta} d\tau e^{i\nu_n \tau} F(\tau). \quad (1)$$

Once one has calculated the correlator $F(\tau)$ analytically, it is a rather easy task to continue its Fourier transform to get the frequency dependent response. However, when numerical techniques are used to evaluate $F(\tau)$, the continuation becomes a serious problem: The Fourier transform is known only for a discrete set of equidistant Matsubara frequencies $\nu_n = 2\pi n/\hbar\beta$. Inserting the spectral representation of the correlation function [9]

$$F(\tau) = \frac{1}{2\pi} \int_{-\infty}^{\infty} d\omega \tilde{F}(\omega) e^{-\tau\omega} \quad (2)$$

with spectral density $\tilde{F}(\omega) \geq 0$ into (1), we find for the conductance

$$G = \frac{\beta}{2} \tilde{F}(0). \quad (3)$$

To relate this with the numerically determined current-current correlation function $F(\tau)$, one has to invert the two-sided Laplace transformation (2). This operation, however, is known as an ill-posed problem: small errors in $F(\tau)$ may cause large deviations in $\tilde{F}(\omega)$. One has to use a regularization scheme to get rid of highly oscillatory functions. Here, we employ SVD [10] regularized by constraints explained below. Before addressing this, we present the QMC algorithm.

Explicitly, the current correlator may be written [8]

$$F(\tau) = 4\pi G_{cl} \alpha(\tau) \langle \cos[\varphi(\tau) - \varphi(0)] \rangle \quad (4)$$

where $G_{\text{cl}} = G_1 G_2 / (G_1 + G_2)$ is the classical high temperature conductance. $\alpha(\tau)$ describes electron-hole pair propagation for electrons and holes created in different electrodes, and may be represented in the form (2)

$$\alpha(\tau) = \frac{1}{2\pi} \int_{-\infty}^{\infty} d\omega \tilde{\alpha}(\omega) e^{-\tau\omega} \quad (5)$$

with the spectral function

$$\tilde{\alpha}(\omega) = \frac{\hbar}{2\pi} \frac{\omega}{1 - e^{-\hbar\beta\omega}}. \quad (6)$$

Finally, the average

$$A(\tau) = \langle \cos[\varphi(\tau) - \varphi(0)] \rangle \quad (7)$$

describes coupling between electron-hole pair excitations and the electromagnetic degrees of freedom, where the time derivative of the phase field $\varphi(\tau)$ is related to the voltage across the SET. To calculate $A(\tau)$, we use a formally exact path integral representation [8]

$$A(\tau) = \frac{1}{Z} \int D[\varphi] e^{-\frac{1}{\hbar} S[\varphi]} \cos[\varphi(\tau) - \varphi(0)], \quad (8)$$

where Z is the partition function and $S[\varphi]$ the Euclidian action that splits into $S[\varphi] = S_C[\varphi] + S_T[\varphi]$. The first term

$$S_C[\varphi] = \int_0^{\hbar\beta} d\tau \left[\frac{\hbar^2 \dot{\varphi}^2(\tau)}{4E_C} + i\hbar n_g \dot{\varphi}(\tau) \right], \quad (9)$$

where $E_C = e^2/2C$ is the charging energy with the island capacitance $C = C_1 + C_2 + C_g$, describes Coulomb charging in presence of a gate voltage $U_g = en_g/C_g$. The second contribution

$$S_T[\varphi] = 2g \int_0^{\hbar\beta} d\tau d\tau' \alpha(\tau - \tau') \sin^2 \left[\frac{\varphi(\tau) - \varphi(\tau')}{2} \right] \quad (10)$$

is due to electron tunneling where $g = (G_1 + G_2)/G_K$ is the dimensionless parallel conductance of the SET.

To implement the topology of the configuration space, we introduce winding numbers k labeling different classes of paths running from $\varphi(0) = 0$ to $\varphi(\hbar\beta) = 2\pi k$. Changing the variables, $\varphi(\tau) = \nu_k \tau + \zeta(\tau)$ with $\zeta(0) = \zeta(\hbar\beta) = 0$, one may integrate out the gate voltage dependent term in Eq. (9), and write

$$A(\tau) = \frac{\langle \langle e^{-2\pi i k n_g} \cos[\nu_k \tau + \zeta(\tau)] \rangle \rangle}{\langle \langle e^{-2\pi i k n_g} \rangle \rangle}, \quad (11)$$

with the unnormalized average over a positive measure

$$\langle \langle X \rangle \rangle = \sum_{k=-\infty}^{\infty} \oint D[\zeta] e^{-\frac{1}{\hbar} S_0[\nu_k \tau + \zeta]} X. \quad (12)$$

Here, $S_0[\zeta]$ is given by Eqs. (9) and (10) with the gate voltage set to zero. Since $S_0[\zeta]$ is real, we may employ

standard Metropolis sampling techniques to evaluate the path integral numerically. For the temperatures explored the data were found to be saturated at Trotter number $N \approx 5\beta E_C$. For higher temperatures we have chosen $N \geq 100$ to keep the resolution of the discretized correlation function high enough for the Laplace inversion. The QMC data show statistical errors of at most 3% for all temperatures and gate voltages. The denominator $\langle \langle \exp(-2\pi i k n_g) \rangle \rangle$ in Eq. (11) is an averaged sign factor that always exceeds 0.04 for the results shown below.

To analyse the data we start by noting that $A(\tau)$ also has a representation of the form (2). In terms of the spectral functions we then find

$$\tilde{F}(\omega) = 2G_{\text{cl}} \int_{-\infty}^{\infty} d\omega' \tilde{\alpha}(\omega - \omega') \tilde{A}(\omega'). \quad (13)$$

In view of the symmetry $A(\tau) = A(\hbar\beta - \tau)$ equivalent to detailed balance $\tilde{A}(-\omega) = e^{-\hbar\beta\omega} \tilde{A}(\omega)$, we may introduce the positive and symmetric spectral function

$$\tilde{A}'(\omega) = \tilde{A}(\omega) \frac{1 - e^{-\hbar\beta\omega}}{\omega} \quad (14)$$

and write

$$A(\tau) = \frac{1}{2\pi} \int_0^{\infty} d\omega \tilde{A}'(\omega) K_{\beta}(\omega, \tau) \quad (15)$$

with the integration kernel

$$K_{\beta}(\omega, \tau) = \frac{\omega}{1 - e^{-\hbar\beta\omega}} \left[e^{-\omega\tau} + e^{-\omega(\hbar\beta - \tau)} \right]. \quad (16)$$

Now, we may restrict the time domain to $\tau \in [0, \hbar\beta/2]$. To invert the integral transform (15) consider the operator $\mathcal{K}_{\beta}$ with kernel $K_{\beta}(\omega, \tau)$

$$g(\tau) = (\mathcal{K}_{\beta} \tilde{g})(\tau) = \int_0^{\omega_{\text{max}}} d\omega K_{\beta}(\omega, \tau) \tilde{g}(\omega), \quad (17)$$

and its adjoint $\mathcal{K}_{\beta}^*$

$$\tilde{f}(\omega) = (\mathcal{K}_{\beta}^* f)(\omega) = \int_0^{\hbar\beta/2} d\tau K_{\beta}(\omega, \tau) f(\tau). \quad (18)$$

Clearly, the operation $\mathcal{K}_{\beta} \mathcal{K}_{\beta}^*$ is self-adjoint and positive. The eigenvalue equation

$$(\mathcal{K}_{\beta} \mathcal{K}_{\beta}^* f_n)(\tau) = \mu_n^2 f_n(\tau) \quad (19)$$

can be solved numerically by discretizing the corresponding integral equation. The resulting eigenfunctions form an orthonormal basis $\{f_n(\tau)\}$ in $L^2[0, \hbar\beta/2]$. Now, the spectral function $\tilde{A}'(\omega)$ can be expanded as

$$\tilde{A}'(\omega) \approx \sum_{n=1}^{n_{\text{max}}} \frac{c_n}{\mu_n^2} (\mathcal{K}_{\beta}^* f_n)(\omega), \quad (20)$$

where the

$$c_n = \int_0^{\hbar\beta/2} d\tau A(\tau) f_n(\tau) \quad (21)$$

are expansion coefficients. Eq. (20) explicitly represents $\tilde{A}(\omega)$ in terms of $A(\tau)$ and serves as inverse of the integral transform (15). Since with increasing n the eigenvalues μ_n vanish overexponentially, for large n highly oscillatory parts become more pronounced when the expansion coefficients c_n do not vanish fast enough. This exhibits the origin of the ill-posed problem: a small error becomes amplified by a large inverse singular value $1/\mu_n^2$ and thus a regularization of the procedure is required.

First, the integral in Eq. (17) is cut off at a frequency $\omega_{\max}$ which is chosen so large that the singular functions do not alter appreciably with this cutoff. Second, the sum in Eq. (20) is truncated at $n_{\max}$. To fix the value of $n_{\max}$ we use the noise level

$$\sigma = \sqrt{\frac{1}{N+1} \sum_{i=0}^N \sigma(\tau_i)^2} \quad (22)$$

of the data where N is the Trotter number and $\sigma(\tau_i)$ the standard deviation of the data $A(\tau_i)$. This has to be compared with the error stemming from the truncated expansion in orthonormal functions

$$\epsilon_n = \sqrt{\frac{1}{N+1} \sum_{i=0}^N \left(\sum_{k=1}^n c_k f_k(\tau_i) - A(\tau_i) \right)^2}. \quad (23)$$

To ensure that we do not include fine structure originating from the noise of the QMC data, we fix $n_{\max}$ by demanding $\epsilon_{n_{\max}} \approx \sigma$.

An essential step is to use additional information to regularize the SVD scheme. We know that $\tilde{A}'$ is positive, symmetric, vanishes for large frequencies, and must obey the sum-rule

$$\int_{-\infty}^{\infty} d\omega \tilde{A}'(\omega) \frac{\omega}{1 - e^{-\hbar\beta\omega}} = A(0) = 1. \quad (24)$$

To incorporate this, we make the ansatz

$$\tilde{A}'_M(\omega) = \sum_{n=1}^M \frac{a_n}{\mu_n^2} (\mathcal{K}_\beta^* f_n)(\omega) \quad (25)$$

where $M > n_{\max}$. The coefficients a_n are determined from minimizing a functional according to three constraints. The *proximity* of the solution to the QMC-correlation function is obtained by minimizing

$$\Phi_{\text{prox}}(a_1, \dots, a_{n_{\max}}) = \sum_{n=1}^{n_{\max}} \frac{(c_n - a_n)^2}{2\sigma_n^2}, \quad (26)$$

where the c_n are the expansion coefficients (21) and where the points are weighted according to errors in the

QMC data. To achieve *positivity* we minimize the integral

$$\Phi_{\text{pos}}(a_1, \dots, a_M) = \int d\omega \tilde{A}'_M(\omega)^2 w(\omega), \quad (27)$$

where the weight function vanishes in the region where the result (20) is positive. To account for the *sum-rule* we minimize the functional

$$\Phi_{\text{sum}}(a_1, \dots, a_M) = \left(1 - \int_{-\omega_{\max}}^{\omega_{\max}} d\omega \frac{\omega \tilde{A}'_M(\omega)}{1 - e^{-\hbar\beta\omega}} \right)^2. \quad (28)$$

Overall we have to consider the linear combination

$$\Phi(a_1, \dots, a_M) = \Phi_{\text{prox}} + \lambda \Phi_{\text{pos}} + \mu \Phi_{\text{sum}} \quad (29)$$

with two regularization parameters λ and μ . Differentiating (29) with respect to a_n we get a system of linear equations that may be solved. We have tested the method with analytical functions corrupted by Gaussian noise to optimize the regularization parameters.

After extracting $\tilde{A}'(\omega)$ from the QMC data via SVD, we obtain $\tilde{F}(\omega)$ from the convolution (13) and the conductance from Eq. (3). Varying the gate voltage U_g the conductance shows a periodic behavior and we may define a maximum $G_{\max} = G|_{n_g=\frac{1}{2}}$ and a minimum $G_{\min} = G|_{n_g=0}$ conductance in dependence on temperature.

To estimate error bars we add a further functional to (29): We try to minimize the distance of $\tilde{F}(\omega)$ to a fictive either too low or too high value $\tilde{F}^\pm(\omega)$. This fictive value of the conductance still has to be in accordance with the other three constraints and leads to an upper and lower bound of possible conductance [11]. The error bars for the conductance found by this procedure lie all below 3%. Since they are of the order of the symbol sizes they will be omitted in the figures.

As a first test of the approach we compare our numerical data with second order perturbative results [6] and with semiclassical findings [7,8]. The comparison in Fig. 1 shows that our results agree well with both limiting analytical theories in their ranges of applicability and therefore bridge between the regions of parameters covered by analytical work.

Recently, P. Joyez *et al.* [3] and D. Chouvaev *et al.* [4] have measured the conductance of SETs in the moderately-to-strong tunneling regime. The strong tunneling data by Chouvaev *et al.* cover only a restricted range of temperatures and were found to be in agreement with semiclassical theory. In contrast, some of the data obtained by Joyez *et al.* are not only outside of the range of the perturbative theory but also explore temperatures low enough to show strong deviations from semiclassical results.

However, the experimental data in Ref. [3] for strong tunneling “ $g = 7.3$ ” are found to deviate significantly

from our predictions for $g = 7.3$ (data not shown). Therefore, we have reexamined the parameters given in Ref. [3]: The bare charging energy E_C was determined independently from resonances in the superconducting state that should be reliable within errors of about 10%. The series conductance was measured at sufficiently high temperatures ($\beta E_C = 0.18$) fixing G_{cl} up to a small error. Assuming identical tunnel junctions, the dimensionless parallel conductance was estimated as $g = 4G_{cl}/G_K$. This assumption was consistent with a fit (dashed line in inset of Fig. 2) of the high temperature data to the prediction $G/G_{cl} = 1 - \beta E_C^*/3$ with

$$E_C^*/E_C = 1 - (9g\zeta(3)/2\pi^4 + c)\beta E_C \quad (30)$$

where $c = 0$. Yet, the correct result reads $c = 1/5$ [8,12] leading to the dashed-dotted line in the inset which is inconsistent with the data. Even for the highest temperatures explored experimentally, the data should be compared with the full semiclassical prediction from Ref. [8]. As can be seen from the inset in Fig. 2, the high temperature data are only consistent with a parallel conductance near $g = 10$ implying an asymmetry of the transistor.

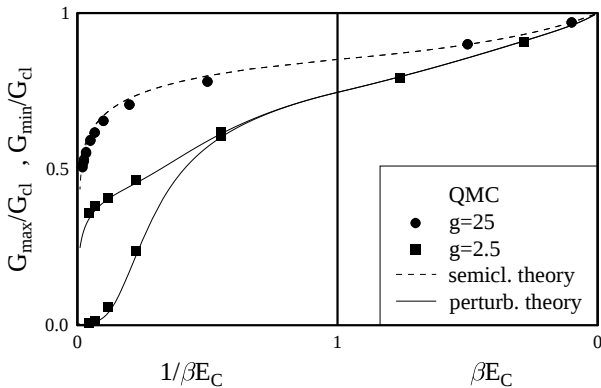


FIG. 1. Predictions for the maximum and minimum linear conductance of a SET for dimensionless parallel conductance $g = 2.5$ compared to second order perturbative results [6] and for $g = 25$ compared to semiclassical findings [7,8].

In Fig. 2 we show for $g = 10$ QMC predictions for maximum and minimum linear conductance in dependence on the inverse temperature. They are compared with the experimental findings from Ref. [3] for “ $g = 7.3$ ” and are found to be in good agreement. The error bounds of the numerical data are again within the symbol size. The parameters for the QMC were not adjusted to improve the global fit but coincide with those extracted from the high temperature analysis. Remaining deviations between the experimental data and our predictions may result from the uncertainty of the parameters.

In summary we have presented a general approach to calculate the conductance of the SET for arbitrary parameters. We found good agreement with limiting analytical theories and could explain experimental findings for highly transmitting tunnel junctions. As one of the

results of this study future experiments in the strong tunneling regime should explore the high temperature behavior of the SET more carefully to allow for a unique parameter identification within the range of validity of the semiclassical theory.

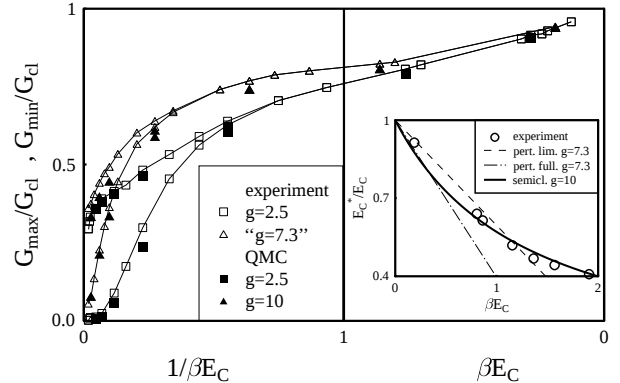


FIG. 2. Predictions for the maximum and minimum linear conductance of a SET for dimensionless parallel conductance $g = 2.5$ and $g = 10$ compared with experimental findings from Ref. [3]. In the inset the experimental data of the renormalized charging energy E_C^*/E_C for “ $g = 7.3$ ” are shown and compared with high temperature approximations (see main text).

The authors would like to thank the authors of Ref. [3] for valuable discussions. One of us (GG) acknowledges hospitality of the CEA-Saclay during an extended stay. Financial support was provided by the Deutsche Forschungsgemeinschaft (DFG), the Deutscher Akademischer Austauschdienst (DAAD), and the MINERVA Foundation (Munich).

- [1] *Single Charge Tunneling*, Vol. 294 of *NATO ASI Series B*, edited by H. Grabert and M. H. Devoret (Plenum, New York, 1992).
- [2] M. A. Kastner, *Rev. Mod. Phys.* **64**, 849 (1992).
- [3] P. Joyez *et al.*, *Phys. Rev. Lett.* **79**, 1349 (1997).
- [4] D. Chouvaev, L. S. Kuzmin, D. S. Golubev, and A. D. Zaikin, *Phys. Rev. B* **59**, 10599 (1999).
- [5] G. L. Ingold and Y. V. Nazarov, in Ref. [1].
- [6] J. König, H. Schoeller, and G. Schön, *Phys. Rev. Lett.* **78**, 4482 (1997).
- [7] D. S. Golubev and A. D. Zaikin, *JETP Lett.* **63**, 1007 (1996). For a review on path integral techniques for tunnel junctions see *e.g.* G. Schön and A. D. Zaikin, *Phys. Rep.* **198**, 237 (1990).
- [8] G. Göppert and H. Grabert, *Phys. Rev. B* **58**, R10155 (1998), and references therein.
- [9] G. Baym and N. D. Mermin, *J. Math. Phys.* **2**, 232 (1961).
- [10] C. E. Creffield, E. G. Klepfish, E. R. Pike, and S. Sarkar, *Phys. Rev. Lett.* **75**, 517 (1995).
- [11] B. Hüpfer, (in preparation).
- [12] D. S. Golubev *et al.*, *Phys. Rev. B* **56**, 15782 (1997).